Renesas Electronics America Inc - R5F2LA88ADFP#30 Datasheet

Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	LCD, POR, PWM, Voltage Detect, WDT
Number of I/O	72
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	3.5K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f2la88adfp-30

1.3 Block Diagrams

Figure 1.5 shows a Block Diagram of R8C/LA3A Group. Figure 1.6 shows a Block Diagram of R8C/LA5A Group. Figure 1.7 shows a Block Diagram of R8C/LA6A Group. Figure 1.8 shows a Block Diagram of R8C/LA8A Group.

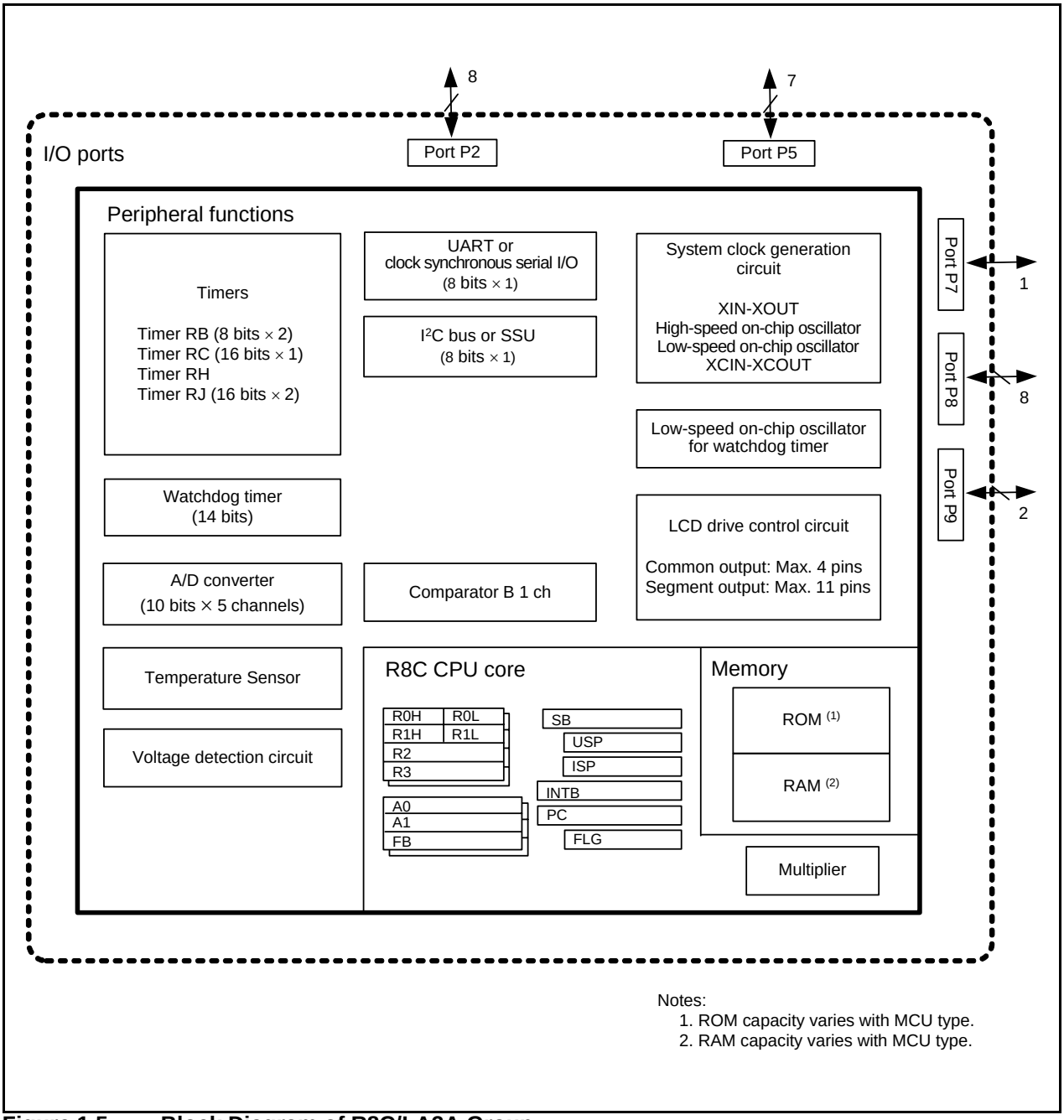
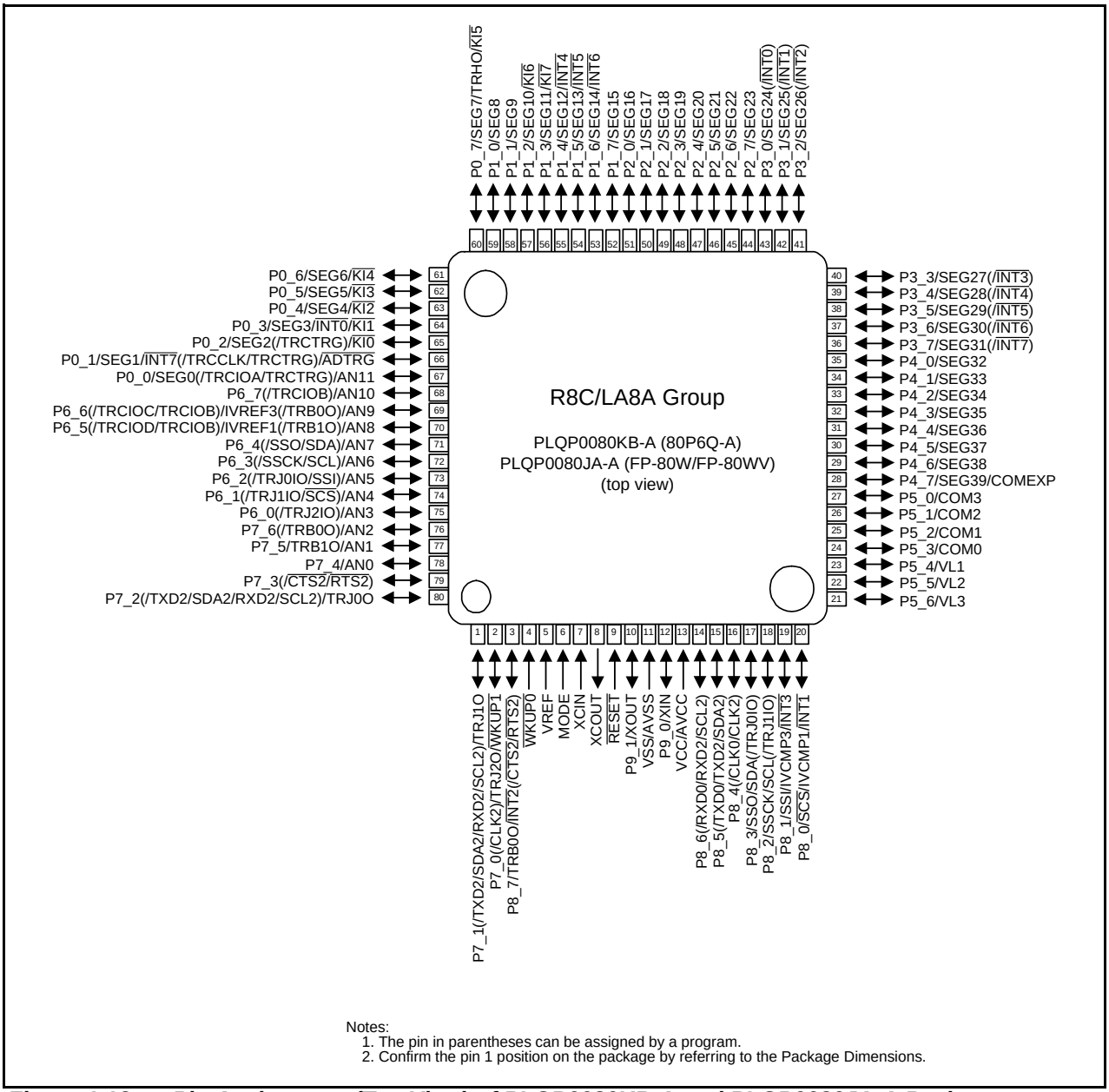


Figure 1.5 Block Diagram of R8C/LA3A Group



Notes:
1. The pin in parentheses can be assigned by a program.
2. Confirm the pin 1 position on the package by referring to the Package Dimensions.

Figure 1.12 Pin Assignment (Top View) of PLQP0080KB-A and PLQP0080JA-A Packages

Table 1.17 Pin Name Information by Pin Number (R8C/LA6A Group, R8C/LA8A Group)(3)

Pin Number		Control Pin	Port	I/O Pin Functions for Peripheral Modules						
LA8A	LA6A			Interrupt	Timer	Serial Interface	SSU	I^2C bus	A/D Converter, Comparator B	LCD drive Control Circuit
69	58		P6_6		(TRB0O/ TRCIOB/ TRCIOC)				AN9/IVREF3	
70	59		P6_5		(TRB1O/ TRCIOB/ TRCIOD)				AN8/IVREF1	
71	60		P6_4				(SSO)	(SDA)	AN7	
72	61		P6_3				(SSCK)	(SCL)	AN6	
73	62		P6_2		(TRJ0IO)		(SSI)		AN5	
74	63		P6_1		(TRJ1IO)		($\overline{SCS}$)		AN4	
75			P6_0		(TRJ2IO)				AN3	
76			P7_6		(TRB0O)				AN2	
77			P7_5		TRB1O				AN1	
78			P7_4						AN0	
79			P7_3			($\overline{CTS2}$/$\overline{RTS2}$)				
80			P7_2		TRJ0O	(RXD2/SCL2/ TXD2/SDA2)				

Note:
1. The pin in parentheses can be assigned by a program.

Table 1.19 Pin Functions for R8C/LA5A Group (2)

Item	Pin Name	I/O Type	Description
I^2C bus	SCL	I/O	Clock I/O pin.
	SDA	I/O	Data I/O pin.
SSU	SSI	I/O	Data I/O pin.
	$\overline{SCS}$	I/O	Chip-select signal I/O pin.
	SSCK	I/O	Clock I/O pin.
	SSO	I/O	Data I/O pin.
Reference voltage input	VREF	I	Reference voltage input pin for the A/D converter.
A/D converter	AN0 to AN6	I	A/D converter analog input pins.
	$\overline{ADTRG}$	I	AD external trigger input pin.
Comparator B	IVCMP1, IVCMP3	I	Comparator B analog voltage input pins.
	IVREF1, IVREF3	I	Comparator B reference voltage input pins.
I/O ports	P0_0 to P0_7, P2_0 to P2_7, P3_0 to P3_7, P5_0 to P5_6, P7_0 to P7_2, P8_0 to P8_7, P9_0, P9_1	I/O	CMOS I/O ports. Each port has an I/O select direction register, allowing each pin in the port to be directed for input or output individually. Any port set to input can be set to use a pull-up resistor or not by a program. Port P8 can be used as LED drive ports.
Segment output	SEG0 to SEG26	O	LCD segment output pins.
Common output	COM0 to COM3, COMEXP	O	LCD common output pins.
LCD power supply	VL1	I	Apply the following voltage: 1 V ≤ VL1 ≤ VCC and VL1 ≤ VL2.
	VL2	I	Apply the following voltage: VL2 ≤ 5.5 V and VL1 ≤ VL2 ≤ VL3.
	VL3	I	Apply the following voltage: VL3 ≤ 5.5 V and VL2 ≤ VL3.

I: Input O: Output I/O: Input and output

Note:

1. Contact the oscillator manufacturer for oscillation characteristics.

Table 4.2 SFR Information for R8C/LA5A Group (2) (1)

Address	Register	Symbol	After Reset
003Ah	Voltage Monitor 2 Circuit Control Register	VW2C	10000010b
003Bh			
003Ch			
003Dh			
003Eh			
003Fh			
0040h			
0041h	Flash Memory Ready Interrupt Control Register	FMRDYIC	XXXXX000b
0042h			
0043h	INT7 Interrupt Control Register	INT7IC	XX00X000b
0044h			
0045h	INT5 Interrupt Control Register	INT5IC	XX00X000b
0046h			
0047h	Timer RC Interrupt Control Register	TRCIC	XXXXX000b
0048h			
0049h			
004Ah	Timer RH Interrupt Control Register	TRHIC	XXXXX000b
004Bh			
004Ch			
004Dh	Key Input Interrupt Control Register	KUPIC	XXXXX000b
004Eh	A/D Conversion Interrupt Control Register	ADIC	XXXXX000b
004Fh	SSU Interrupt Control Register / IIC bus Interrupt Control Register (2)	SSUIC/IICIC	XXXXX000b
0050h			
0051h	UART0 Transmit Interrupt Control Register	S0TIC	XXXXX000b
0052h	UART0 Receive Interrupt Control Register	S0RIC	XXXXX000b
0053h			
0054h			
0055h	INT2 Interrupt Control Register	INT2IC	XX00X000b
0056h	Timer RJ0 Interrupt Control Register	TRJ0IC	XXXXX000b
0057h	Timer RB1 Interrupt Control Register	TRB1IC	XXXXX000b
0058h	Timer RB0 Interrupt Control Register	TRB0IC	XXXXX000b
0059h	INT1 Interrupt Control Register	INT1IC	XX00X000b
005Ah	INT3 Interrupt Control Register	INT3IC	XX00X000b
005Bh	Timer RJ1 Interrupt Control Register	TRJ1IC	XXXXX000b
005Ch			
005Dh	INT0 Interrupt Control Register	INT0IC	XX00X000b
005Eh			
005Fh			
0060h			
0061h			
0062h			
0063h			
0064h			
0065h			
0066h			
0067h			
0068h			
0069h			
006Ah	LCD Interrupt Control Register	LCDIC	XXXXX000b
006Bh			
006Ch			
006Dh			
006Eh			
006Fh			
0070h			
0071h			
0072h	Voltage monitor 1 Interrupt Control Register	VCMP1IC	XXXXX000b
0073h	Voltage monitor 2 Interrupt Control Register	VCMP2IC	XXXXX000b
0074h			
0075h			
0076h			
0077h			
0078h			
0079h			
007Ah			
007Bh			
007Ch			
007Dh			
007Eh			
007Fh			

X: Undefined

Notes:

1. Blank spaces are reserved. No access is allowed.
2. Selectable by the IICSEL bit in the SSUIICSR register.

Table 4.19 ID Code Areas and Option Function Select Area

Address	Area Name	Symbol	After Reset
:			
FFDBh	Option Function Select Register 2	OFS2	(Note 1)
:			
FFDFh	ID1		(Note 2)
:			
FFE3h	ID2		(Note 2)
:			
FFEBh	ID3		(Note 2)
:			
FFEFh	ID4		(Note 2)
:			
FFF3h	ID5		(Note 2)
:			
FFF7h	ID6		(Note 2)
:			
FFFBh	ID7		(Note 2)
:			
FFFFh	Option Function Select Register	OFS	(Note 1)

Notes:
1. The option function select area is allocated in the flash memory, not in the SFRs. Set appropriate values as ROM data by a program.
   Do not write additions to the option function select area. If the block including the option function select area is erased, the option function select area is set to FFh.
   When blank products are shipped, the option function select area is set to FFh. It is set to the written value after written by the user.
   When factory-programming products are shipped, the value of the option function select area is the value programmed by the user.
2. The ID code areas are allocated in the flash memory, not in the SFRs. Set appropriate values as ROM data by a program.
   Do not write additions to the ID code areas. If the block including the ID code areas is erased, the ID code areas are set to FFh.
   When blank products are shipped, the ID code areas are set to FFh. They are set to the written value after written by the user.
   When factory-programming products are shipped, the value of the ID code areas is the value programmed by the user.

5.1.3 Peripheral Function Characteristics

Table 5.3 A/D Converter Characteristics
(Vcc/AVcc = Vref = 1.8 to 5.5 V, Vss = 0 V, and Topr = –20 to 85 °C (N version)/ –40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter		Conditions		Standard			Unit
					Min.	Typ.	Max.	
–	Resolution		Vref = AVcc		–	–	10	Bit
–	Absolute accuracy (2)	10-bit mode	Vref = AVcc = 5.0 V	AN0 to AN6 input	–	–	±3	LSB
			Vref = AVcc = 2.2 V	AN0 to AN6 input	–	–	±5	LSB
			Vref = AVcc = 1.8 V	AN0 to AN6 input	–	–	±5	LSB
		8-bit mode	Vref = AVcc = 5.0 V	AN0 to AN6 input	–	–	±2	LSB
			Vref = AVcc = 2.2 V	AN0 to AN6 input	–	–	±2	LSB
			Vref = AVcc = 1.8 V	AN0 to AN6 input	–	–	±2	LSB
ϕAD	A/D conversion clock		4.0 ≤ Vref = AVcc ≤ 5.5 V (1)		1	–	20	MHz
			3.2 ≤ Vref = AVcc ≤ 5.5 V (1)		1	–	16	MHz
			2.7 ≤ Vref = AVcc ≤ 5.5 V (1)		1	–	10	MHz
			1.8 ≤ Vref = AVcc ≤ 5.5 V (1)		1	–	8	MHz
–	Tolerance level impedance				–	3	–	kΩ
tCONV	Conversion time	10-bit mode	Vref = AVcc = 5.0 V, ϕAD = 20 MHz		2.2	–	–	µs
		8-bit mode	Vref = AVcc = 5.0 V, ϕAD = 20 MHz		2.2	–	–	ms
tSAMP	Sampling time		ϕAD = 20 MHz		0.8	–	–	µs
IVref	Vref current		Vcc = 5 V, XIN = f1 = ϕAD = 20 MHz		–	45	–	µA
Vref	Reference voltage				1.8	–	AVcc	V
VIA	Analog input voltage (3)				0	–	Vref	V
OCVREF	On-chip reference voltage		2 MHz ≤ ϕAD ≤ 4 MHz		1.53	1.70	1.87	V

Notes:
1. The A/D conversion result will be undefined in wait mode, stop mode, power-off mode, when the flash memory stops, and in low-current-consumption mode. Do not perform A/D conversion in these states or transition to these states during A/D conversion.
2. This applies when the peripheral functions are stopped.
3. When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

Table 5.4 Temperature Sensor Characteristics
(Vss = 0 V and Topr = –20 to 85 °C (N version)/ –40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
VTMP	Temperature sensor output voltage	1.8 V ≤ Vref = AVcc ≤ 5.5 V ϕAD = 1.0 MHz to 5.0 MHz Ambient temperature = 25 °C	550	600	650	mV
–	Temperature coefficient	1.8 V ≤ Vref = AVcc ≤ 5.5 V ϕAD = 1.0 MHz to 5.0 MHz Ambient temperature = 25 °C	–	–2.1	–	mV/°C
–	Start-up time	1.8 V ≤ Vref = AVcc ≤ 5.5 V ϕAD = 1.0 MHz to 5.0 MHz	–	–	200	µs
ITMP	Operating current	1.8 V ≤ Vref = AVcc ≤ 5.5 V ϕAD = 1.0 MHz to 5.0 MHz	–	100	–	µA

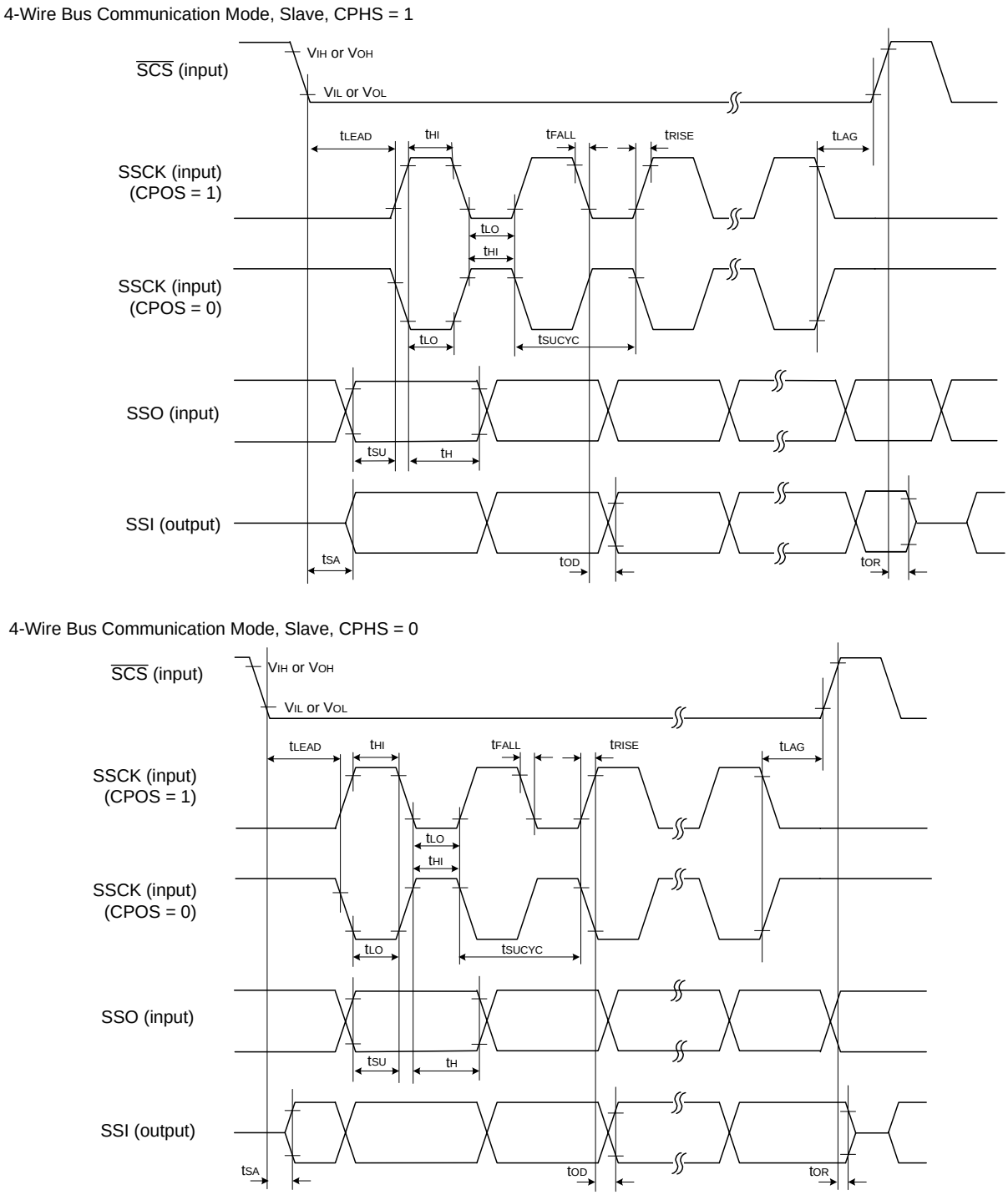


Figure 5.5 I/O Timing of Synchronous Serial Communication Unit (SSU) (Slave)

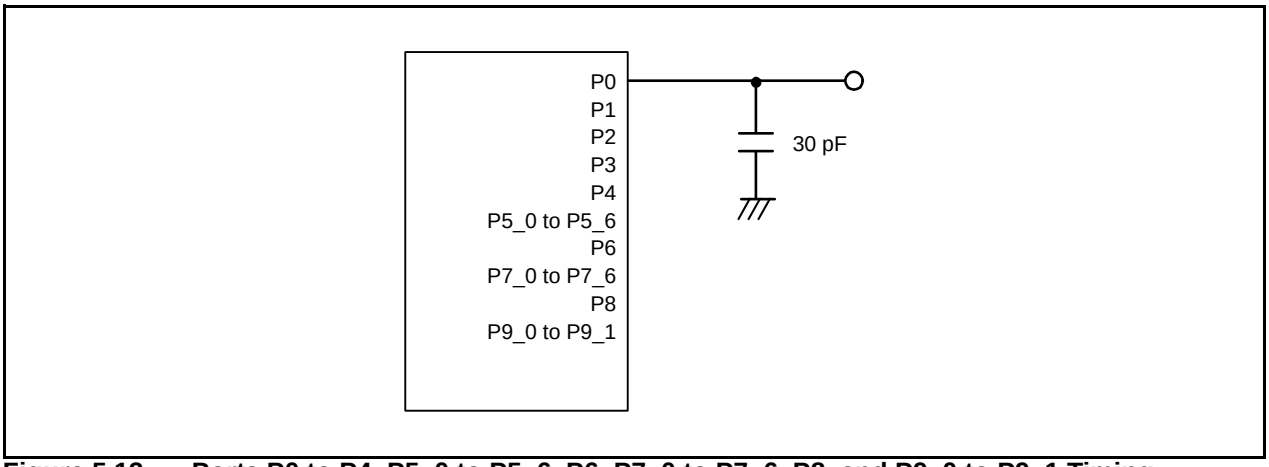


Figure 5.12 Ports P0 to P4, P5_0 to P5_6, P6, P7_0 to P7_6, P8, and P9_0 to P9_1 Timing Measurement Circuit

Table 5.34 Gain Amplifier Characteristics
(VSS = 0 V and Topr = –20 to 85 °C (N version)/–40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
VGAIN	Gain amplifier operating range		0.4	–	AVCC – 1.0	V
ϕAD	A/D conversion clock		1	–	5	MHz

Table 5.35 Comparator B Characteristics
(VCC = 1.8 to 5.5 V and Topr = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
Vref	IVREF1, IVREF3 input reference voltage		0	–	VCC – 1.4	V
VI	IVCMP1, IVCMP3 input voltage		-0.3	–	VCC + 0.3	V
–	Offset		–	5	100	mV
td	Comparator output delay time (1)	VI = Vref ± 100 mV	–	–	1	µs
ICMP	Comparator operating current	VCC = 5.0 V	–	12	–	µA

Note:
1. When the digital filter is disabled.

Table 5.36 Flash Memory (Program ROM) Characteristics
(VCC = 1.8 to 5.5 V and Topr = 0 to 60°C, unless otherwise specified.)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance (1)		10,000 (2)	–	–	times
–	Byte program time		–	80	–	µs
–	Block erase time	Internal ROM Capacity: 16 KB, 32 KB, 48 KB, 64 KB	–	0.12	–	s
		Internal ROM Capacity: 96 KB, 128 KB	–	0.2	–	s
td(SR-SUS)	Time delay from suspend request until suspend		–	–	0.25 + CPU clock × 3 cycles	ms
–	Time from suspend until erase restart		–	–	30 + CPU clock × 1 cycle	µs
td(CMDRST-READY)	Time from when command is forcibly terminated until reading is enabled		–	–	30 + CPU clock × 1 cycle	µs
–	Program, erase voltage		1.8	–	5.5	V
–	Read voltage		1.8	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time (6)	Ambient temperature = 85°C	10	–	–	year

Notes:
1. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
2. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
3. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
4. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
5. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
6. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.37 Flash Memory (Data flash Block A and Block B) Characteristics (Vcc = 1.8 to 5.5 V and Topr = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance (1)		10,000 (2)	–	–	times
–	Byte program time (program/erase endurance ≤ 10,000 times)		–	150	–	µs
–	Block erase time (program/erase endurance ≤ 10,000 times)	Internal ROM Capacity: 1 KB × 2	–	0.05	1	s
		Internal ROM Capacity: 2 KB × 2	–	0.055	1	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	0.25 + CPU clock × 3 cycles	ms
–	Time from suspend until erase restart		–	–	30 + CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly terminated until reading is enabled		–	–	30 + CPU clock × 1 cycle	µs
–	Program, erase voltage		1.8	–	5.5	V
–	Read voltage		1.8	–	5.5	V
–	Program, erase temperature		–20 (6)	–	85	°C
–	Data hold time (7)	Ambient temperature = 85 °C	10	–	–	year

Notes:
1. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
2. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
3. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A and B can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
4. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
5. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
6. –40°C for D version.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

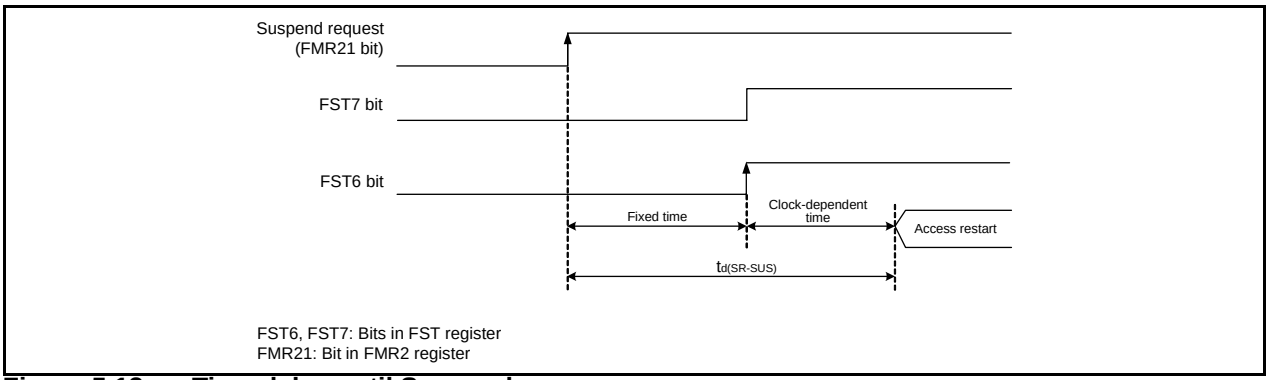


Figure 5.13 Time delay until Suspend

Table 5.40 Voltage Detection 2 Circuit Characteristics
(V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

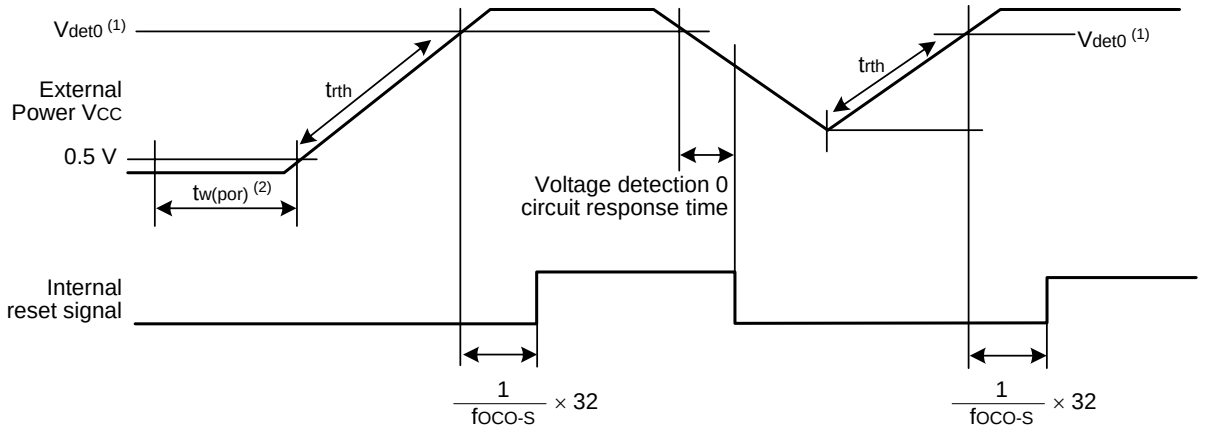
Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
V_{det2}	Voltage detection level Vdet2_0 (1)	At the falling of V_{CC}		3.70	4.0	4.30	V
–	Hysteresis width at the rising of Vcc in voltage detection 2 circuit			–	0.10	–	V
–	Voltage detection 2 circuit response time (2)	In operation	At the falling of Vcc from 5 V to (Vdet2_0 – 0.1) V	–	20	150	µs
		In stop mode	At the falling of Vcc from 5 V to (Vdet2_0 – 0.1) V	–	200	500	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0 V		–	1.7	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (3)			–	–	100	µs

Notes:
1. The voltage detection level varies with detection targets. Select the level with the VCA24 bit in the VCA2 register.
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det2}.
3. Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.

Table 5.41 Power-on Reset Circuit Characteristics (1)
(T_{opr} = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t_{rth}	External power V_{CC} rise gradient		0	–	50000	mV/ms

Note:
1. To use the power-on reset function, enable voltage monitor 0 reset by setting the LVDAS bit in the OFS register to 0.



Notes:
1. V_{det0} indicates the voltage detection level of the voltage detection 0 circuit. Refer to **6. Voltage Detection Circuit** in the User's Manual: Hardware for details.
2. $t_{w(por)}$ indicates the duration the external power V_{CC} must be held below the valid voltage (0.5 V) to enable a power-on reset. When turning on the power after it falls with voltage monitor 0 reset disabled, maintain $t_{w(por)}$ for 1 ms or more.

Figure 5.14 Power-on Reset Circuit Characteristics

5.2.4 DC Characteristics

Table 5.47 DC Characteristics (1) [4.0 V ≤ Vcc ≤ 5.5 V]
(Topr = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter		Condition			Standard			Unit
						Min.	Typ.	Max.	
V_{OH}	Output “H” voltage		Port P7_0, P7_1, P8 (1)	V_{CC} = 5V	I_{OH} = –20 mA	V_{CC} – 2.0	–	V_{CC}	V
			Other pins	V_{CC} = 5V	I_{OH} = –5 mA	V_{CC} – 2.0	–	V_{CC}	V
V_{OL}	Output “L” voltage		Port P7_0, P7_1, P8 (1)	V_{CC} = 5V	I_{OL} = 20 mA	–	–	2.0	V
			Other pins	V_{CC} = 5V	I_{OL} = 5 mA	–	–	2.0	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{INT4}$, $\overline{INT5}$, $\overline{INT6}$, $\overline{INT7}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, $\overline{KI4}$, $\overline{KI5}$, $\overline{KI6}$, $\overline{KI7}$, TRCIOA, TRCIOB, TRCIOC, TRCIOD, TRJ0IO, TRJ1IO, TRJ2IO, $\overline{TRCTRG}$, TRCCLK, $\overline{ADTRG}$, RXD0, RXD2, CLK0, CLK2, SSI, SCL, SDA, SSO				0.05	0.5	–	V
		$\overline{RESET}$, $\overline{WKUP0}$				0.1	0.8	–	V
I_{IH}	Input “H” current		VI = 5 V, V_{CC} = 5 V			–	–	5.0	µA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 5 V			–	–	–5.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 5 V			20	40	80	kΩ
R_{fXIN}	Feedback resistance	XIN				–	2.0	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN				–	14	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode			1.8	–	–	V

Note:
1. This applies when the drive capacity of the output transistor is set to High by registers P7DRR and P8DRR. When the drive capacity is set to Low, the value of any other pin applies.

Table 5.49 DC Characteristics (3) [2.7 V ≤ Vcc < 4.0 V]
(Topr = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage		Port P7_0, P7_1, P8 (1)	I_{OH} = –5 mA	V_{CC} – 0.5	–	V_{CC}	V
			Other pins	I_{OH} = –1 mA	V_{CC} – 0.5	–	V_{CC}	V
V_{OL}	Output “L” voltage		Port P7_0, P7_1, P8 (1)	I_{OL} = 5 mA	–	–	0.5	V
			Other pins	I_{OL} = 1 mA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{INT4}$, INT5, $\overline{INT6}$, $\overline{INT7}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, KI4, KI5, KI6, KI7, TRCIOA, TRCIOB, TRCIOC, TRCIOD, TRJ0IO, TRJ1IO, TRJ2IO, $\overline{TRCTRG}$, TRCCLK, $\overline{ADTRG}$, RXD0, RXD2, CLK0, CLK2, SSI, SCL, SDA, SSO			0.05	0.4	–	V
		$\overline{RESET}$, $\overline{WKUP0}$			0.1	0.8	–	V
I_{IH}	Input “H” current		VI = 3 V, V_{CC} = 3 V		–	–	5.0	µA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 3 V		–	–	–5.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 3 V		25	80	140	kΩ
R_{fXIN}	Feedback resistance	XIN			–	2.0	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	14	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

Note:
1. This applies when the drive capacity of the output transistor is set to High by registers P7DRR and P8DRR. When the drive capacity is set to Low, the value of any other pin applies.

Table 5.50 DC Characteristics (4) [2.7 V ≤ Vcc < 4.0 V]
(Topr = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition								Standard			Unit
			Oscillation Circuit		On-Chip Oscillator		CPU Clock	Low-Power-Consumption Setting	Other	Min.	Typ. (3)	Max.	
			XIN (2)	XCIN	High-Speed	Low-Speed							
Icc	Power supply current (1)	High-speed clock mode	20 MHz	Off	Off	125 kHz	No division	–		–	4.7	10	mA
			10 MHz	Off	Off	125 kHz	No division	–		–	2.3	6	mA
			20 MHz	Off	Off	Off	No division	FMR27 = 1 MSTCR0 = BEh MSTCR1 = 3Fh	Flash memory off Program operation on RAM Module standby setting enabled	–	2.9	–	mA
			20 MHz	Off	Off	125 kHz	Divide-by-8	–		–	1.8	–	mA
			10 MHz	Off	Off	125 kHz	Divide-by-8	–		–	1.0	–	mA
		High-speed on-chip oscillator mode	Off	Off	20 MHz	125 kHz	No division	–		–	5.0	11	mA
			Off	Off	20 MHz	125 kHz	Divide-by-8	–		–	2.1	–	mA
			Off	Off	10 MHz	125 kHz	No division	–		–	2.9	–	mA
			Off	Off	10 MHz	125 kHz	Divide-by-8	–		–	1.5	–	mA
			Off	Off	4 MHz	125 kHz	Divide-by-16	MSTCR0 = BEh MSTCR1 = 3Fh		–	0.9	–	mA
		Low-speed on-chip oscillator mode	Off	Off	Off	125 kHz	No division	FMR27 = 1 VCA20 = 0		–	106	300	µA
			Off	Off	Off	125 kHz	Divide-by-8	FMR27 = 1 VCA20 = 0		–	54	200	µA
		Low-speed clock mode	Off	32 kHz	Off	Off	No division	FMR27 = 1 VCA20 = 0		–	54	200	µA
			Off	32 kHz	Off	Off	No division	FMSTP = 1 VCA20 = 0	Flash memory off Program operation on RAM	–	36	–	µA
		Wait mode	Off	Off	Off	125 kHz	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1	While a WAIT instruction is executed Peripheral clock operation	–	9.0	50	µA
			Off	Off	Off	125 kHz	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM02 = 1 CM01 = 1	While a WAIT instruction is executed Peripheral clock off	–	2.5	31	µA
			Off	32 kHz	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM02 = 1 CM01 = 0	While a WAIT instruction is executed Peripheral clock off Timer RH operation in real-time clock mode LCD drive control circuit (4) When external division resistors are used	–	3.1	–	µA
			Off	32 kHz	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM02 = 1 CM01 = 1	While a WAIT instruction is executed Peripheral clock off Timer RH operation in real-time clock mode	–	1.7	–	µA
		Stop mode	Off	Off	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Topr = 25°C Peripheral clock off	–	0.5	2.2	µA
			Off	Off	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Topr = 85°C Peripheral clock off	–	1.2	–	µA
		Power-off mode	Off	Off	Off	Off	–	–	Power-off 0 Topr = 25°C	–	0.01	0.1	µA
			Off	Off	Off	Off	–	–	Power-off 0 Topr = 85°C	–	0.02	–	µA
			Off	32 kHz	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Power-off 2 Topr = 25°C	–	1.3	4.5	µA
			Off	32 kHz	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Power-off 2 Topr = 85°C	–	2.2	–	µA

Notes:
1. Vcc = 2.7 V to 4.0 V, single chip mode, output pins are open, and other pins are Vss.
2. XIN is set to square wave input.
3. Vcc = 3.0 V
4. VLCD = Vcc, external division resistors are used for VL3 to VL1, 1/3 bias, 1/4 duty, f(FR) = 64 Hz, SEG0 to SEG39 are selected, and segment and common output pins are open. The standard value does not include the current that flows through external division resistors.

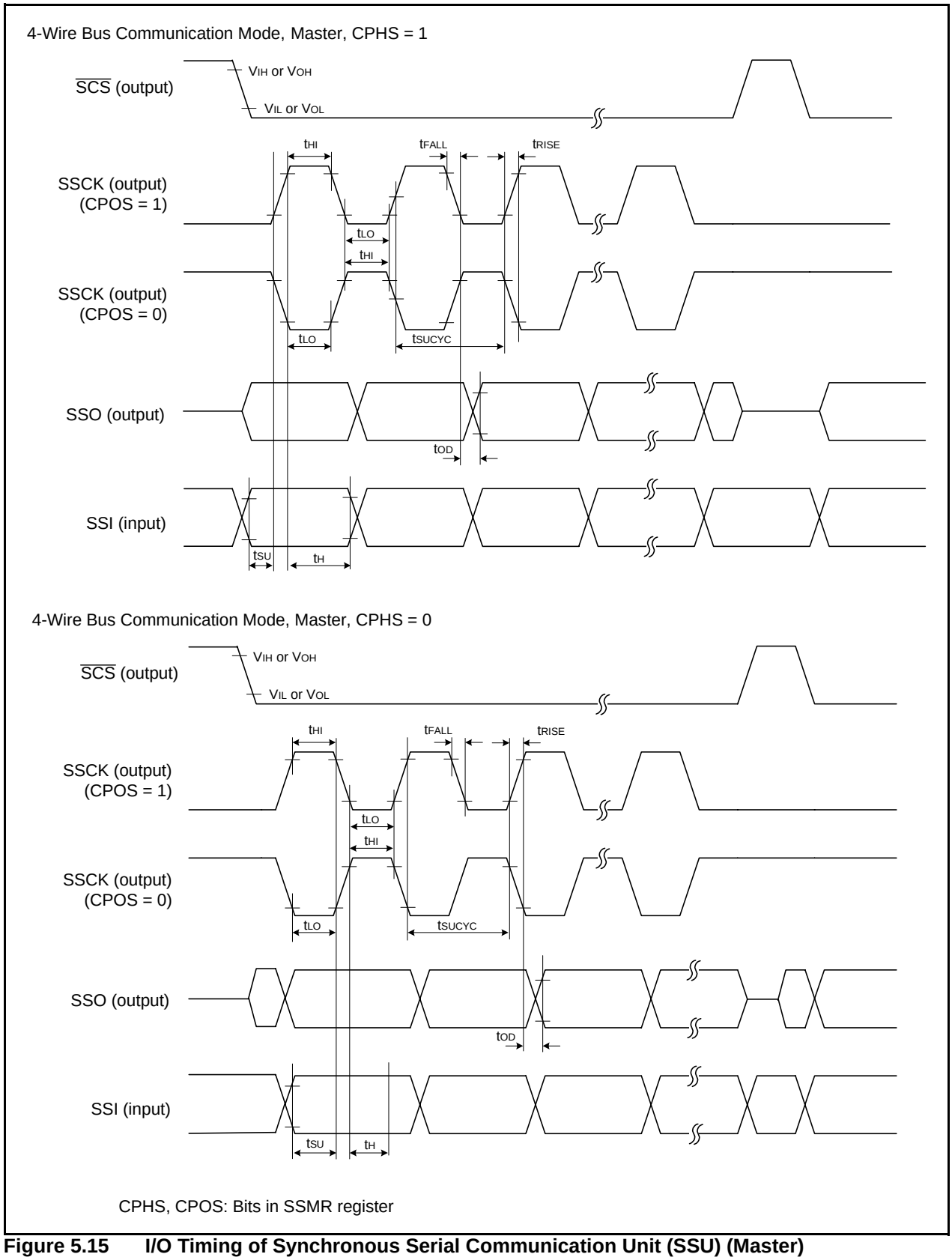


Figure 5.15 I/O Timing of Synchronous Serial Communication Unit (SSU) (Master)

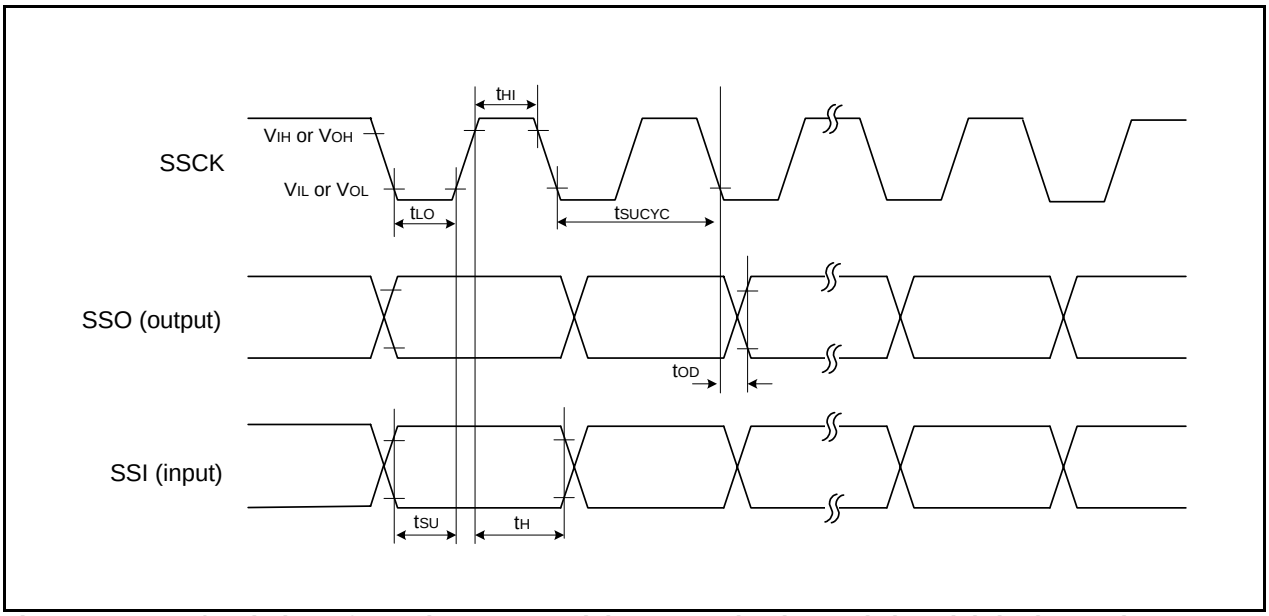
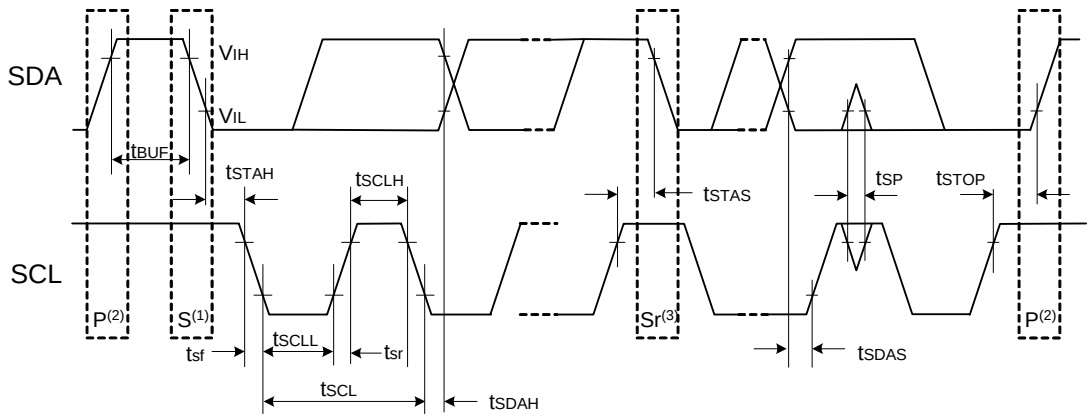


Figure 5.17 I/O Timing of Synchronous Serial Communication Unit (SSU) (Clock Synchronous Communication Mode)

Table 5.54 Timing Requirements of I²C bus Interface (1)
(Vcc = 1.8 to 5.5 V, Vss = 0 V, and Topr = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
tSCL	SCL input cycle time		12tCYC + 600 (1)	–	–	ns
tSCLH	SCL input “H” width		3tCYC + 300 (1)	–	–	ns
tSCLL	SCL input “L” width		5tCYC + 500 (1)	–	–	ns
tsf	SCL, SDA input fall time		–	–	300	ns
tSP	SCL, SDA input spike pulse rejection time		–	–	1tCYC (1)	ns
tBUF	SDA input bus-free time		5tCYC (1)	–	–	ns
tSTAH	Start condition input hold time		3tCYC (1)	–	–	ns
tSTAS	Retransmit start condition input setup time		3tCYC (1)	–	–	ns
tSTOP	Stop condition input setup time		3tCYC (1)	–	–	ns
tSDAS	Data input setup time		1tCYC + 40 (1)	–	–	ns
tSDAH	Data input hold time		10	–	–	ns

Note:
1. 1tCYC = 1/f1(s)



Notes:
1. Start condition
2. Stop condition
3. Retransmit start condition

Figure 5.18 I/O Timing of I²C bus Interface

Table 5.55 Timing Requirements of External Clock Input (XIN, XCIN)
(Vss = 0 V and Topr = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Standard						Unit
		Vcc = 2.2V, Topr = 25°C		Vcc = 3V, Topr = 25°C		Vcc = 5V, Topr = 25°C		
		Min.	Max.	Min.	Max.	Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	200	–	50	–	50	–	ns
$t_{WH(XIN)}$	XIN input “H” width	90	–	24	–	24	–	ns
$t_{WL(XIN)}$	XIN input “L” width	90	–	24	–	24	–	ns
$t_{c(XCIN)}$	XCIN input cycle time	20	–	20	–	20	–	µs
$t_{WH(XCIN)}$	XCIN input “H” width	10	–	10	–	10	–	µs
$t_{WL(XCIN)}$	XCIN input “L” width	10	–	10	–	10	–	µs

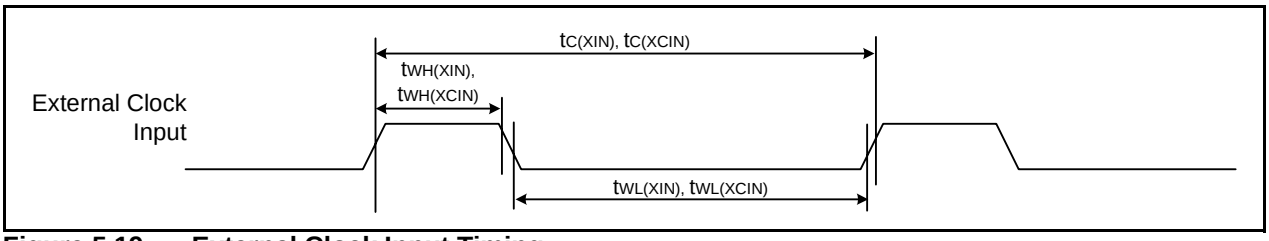


Figure 5.19 External Clock Input Timing

Table 5.56 Timing Requirements of TRJiIO (i = 0 to 2)
(Vss = 0 V and Topr = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Standard						Unit
		Vcc = 2.2V, Topr = 25°C		Vcc = 3V, Topr = 25°C		Vcc = 5V, Topr = 25°C		
		Min.	Max.	Min.	Max.	Min.	Max.	
$t_{c(TRJIO)}$	TRJiIO input cycle time	500	–	300	–	100	–	ns
$t_{WH(TRJIO)}$	TRJiIO input “H” width	200	–	120	–	40	–	ns
$t_{WL(TRJIO)}$	TRJiIO input “L” width	200	–	120	–	40	–	ns

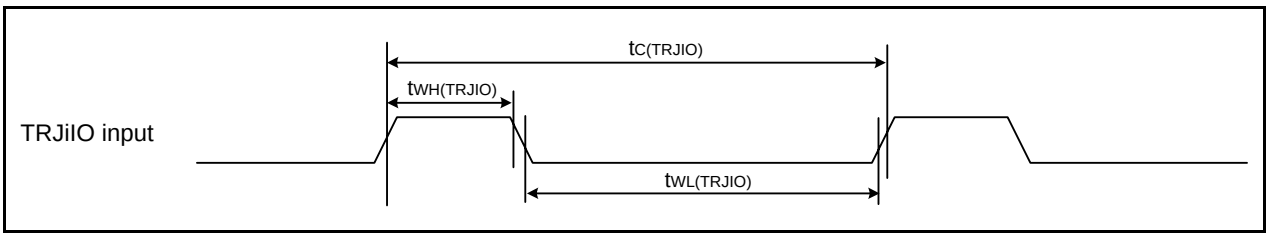


Figure 5.20 Input Timing of TRJiIO

REVISION HISTORY	R8C/LA3A Group, R8C/LA5A Group, R8C/LA6A Group, R8C/LA8A Group Datasheet

Rev.	Date	Description	
		Page	Summary
1.00	Dec 21, 2010	32	"The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh." deleted Figure 3.1 revised
		33 to 41	Tables 4.1 to 4.9 SFR information for R8C/LA5A Group added
		52 to 98	"5. Electrical Characteristics" added
		92	Package Dimensions "PVQN0064LB-A" deleted
1.01	Oct 28, 2011	1	1.1 ".... data flash (1 KB × 2 blocks)." → ".... data flash."
		10	Table 1.11, Figure 1.3 revised
		11	Table 1.12, Figure 1.4 revised
		32	3 revised, Figure 3.1 revised
		60	Table 5.12 revised
		80	Table 5.36 revised
		81	Table 5.37 revised
		83	Table 5.41 revised